

Please amend the application as follows:

In the Claims

Please add new Claims 25 and 26.

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- Excluded*
25. (New) A magnetic field sensor as described in Claim 8, wherein the field sensitivity of the magnetic field sensor is at least 5 mV output signal per Oe of applied magnetic field.
26. (New) A magnetic field sensor as described in Claim 8, wherein the field sensitivity of the magnetic field sensor is at least 10 mV output signal per Oe of applied magnetic field.
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REMARKS

With the entry of the present amendment, claims 6-21 and 23-26 remain pending in the application. Claims 21 and 23 have been withdrawn from consideration as relating to a non-elected invention. Claims 6-20 and 24 stand rejected under 35 U.S.C. §103 as being unpatentable over GB 2188157, to Oetzmann.

New Claim 25 recites that the field sensitivity is at least 5 mV output signal per Oe of applied magnetic field. New Claim 26 recites that the field sensitivity is at least 10 mV output signal per Oe of applied magnetic field. Support for these claims is found in the present specification at, for instance, p. 3, lines 2-4; p. 16, line 9 through p. 17, line 14; and in Figs. 9-11.

The present invention relates to passive solid-state magnetic sensors utilizing magnetostrictive and piezoelectric materials characterized by high magnetic field sensitivity, wide dynamic range, and low cost of manufacture. In one embodiment, the magnetic sensors comprise a layer of magnetostrictive material in contact with a layer of piezoelectric material, and configured such that when the magnetostrictive material is subjected to an alternating magnetic field, a change in at least one dimension of the magnetostrictive material induces a strain in the piezoelectric material, thus producing a detectable voltage signal indicative of the measured magnetic field.